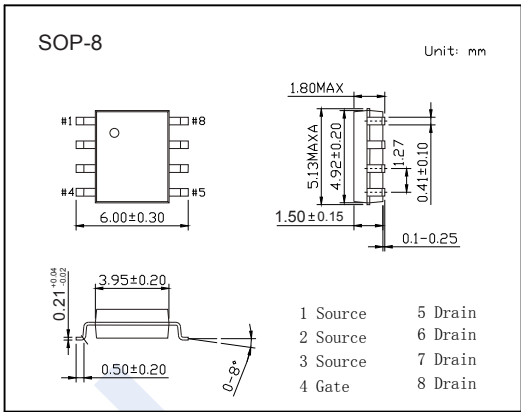
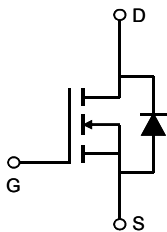


N-Channel MOSFET AO4310 (KO4310)

■ Features

- $V_{DS} (V) = 36V$
- $I_D = 27 A (V_{GS} = 10V)$
- $R_{DS(ON)} < 3.1m\Omega (V_{GS} = 10V)$
- $R_{DS(ON)} < 4.2m\Omega (V_{GS} = 4.5V)$



■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	36	V
Gate-Source Voltage	V_{GS}	±20	
Continuous Drain Current	I_D	27	A
		22	
Pulsed Drain Current	I_{DM}	390	
Avalanche Current	I_{AS}, I_{AR}	67	mJ
Avalanche energy	$L=0.1mH$	224	
Power Dissipation	P_D	3.6	W
		2.3	
Thermal Resistance.Junction- to-Ambient	R_{thJA}	35	$^\circ C/W$
		65	
Thermal Resistance.Junction- to-Lead	R_{thJL}	15	
Junction Temperature	T_J	150	$^\circ C$
Storage Temperature Range	T_{stg}	-55 to 150	

N-Channel MOSFET

AO4310 (KO4310)

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V _{DSS}	I _D =250 μA, V _{GS} =0V	36			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =36V, V _{GS} =0V			1	μA
		V _{DS} =36V, V _{GS} =0V, T _J =55°C			5	
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250μA	1.2		2.3	V
Static Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =10V, I _D =20A			3.1	mΩ
		V _{GS} =10V, I _D =20A, T _J =125°C			4.5	
		V _{GS} =4.5V, I _D =20A			4.2	
On State Drain Current	I _{D(ON)}	V _{GS} =10V, V _{DS} =5V	390			A
Forward Transconductance	g _{FS}	V _{DS} =5V, I _D =20A		151		S
Input Capacitance	C _{iss}	V _{GS} =0V, V _{DS} =18V, f=1MHz	2595		3900	pF
Output Capacitance	C _{oss}		790		1470	
Reverse Transfer Capacitance	C _{rss}		16		95	
Gate Resistance	R _g	V _{GS} =0V, V _{DS} =0V, f=1MHz	0.8		2.7	Ω
Total Gate Charge (10V)	Q _g	V _{GS} =10V, V _{DS} =18V, I _D =20A	37		57	nC
Total Gate Charge (4.5V)			16		27	
Gate Source Charge	Q _{gs}			8		
Gate Drain Charge	Q _{gd}			6.2		
Turn-On DelayTime	t _{d(on)}	V _{GS} =10V, V _{DS} =18V, R _L =0.9Ω, R _{GEN} =3Ω		8.5		ns
Turn-On Rise Time	t _r			4.8		
Turn-Off DelayTime	t _{d(off)}			40.8		
Turn-Off Fall Time	t _f			9.8		
Body Diode Reverse Recovery Time	t _{rr}	I _F = 20A, di/dt= 500A/us	17		26	nC
Body Diode Reverse Recovery Charge	Q _{rr}		48		73	
Maximum Body-Diode Continuous Current	I _S				5	A
Diode Forward Voltage	V _{SD}	I _S =1A, V _{GS} =0V			1	V

Note : The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

■ Marking

Marking	4310 KC****
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N-Channel MOSFET

AO4310 (KO4310)

■ Typical Characteristics

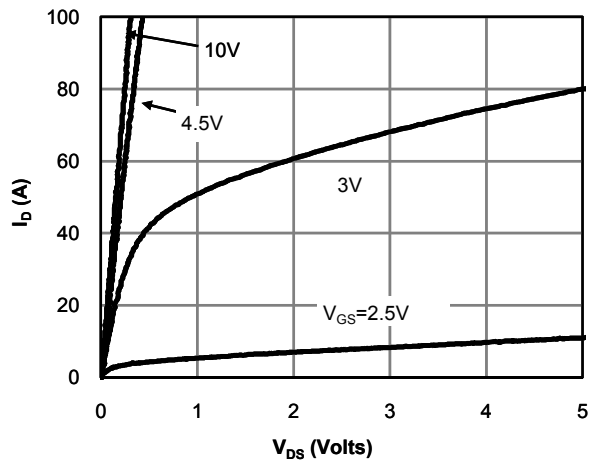


Fig 1: On-Region Characteristics (Note E)

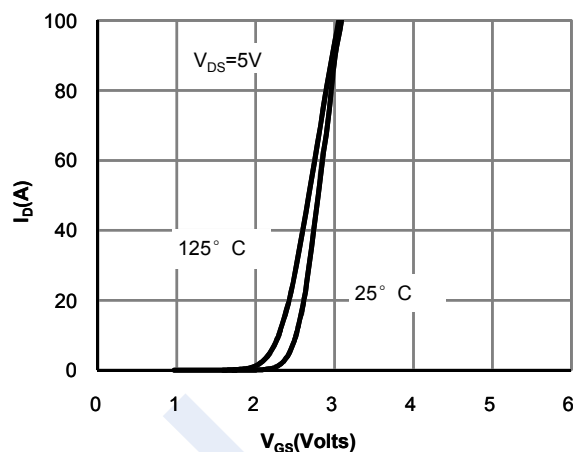


Figure 2: Transfer Characteristics (Note E)

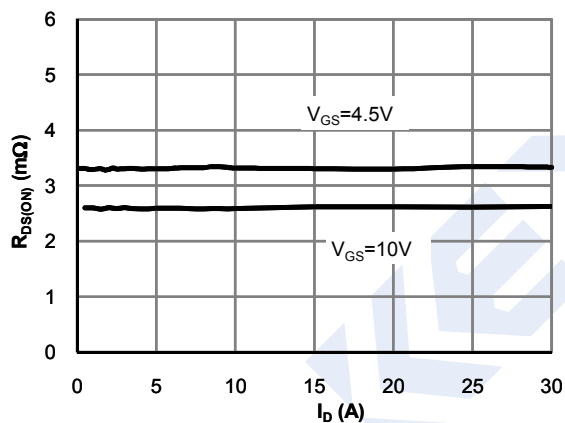


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

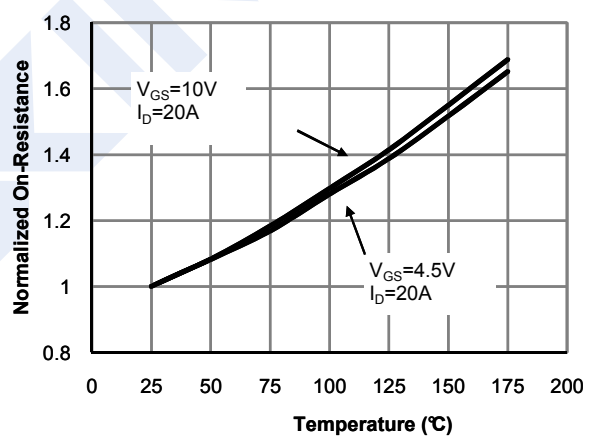


Figure 4: On-Resistance vs. Junction Temperature (Note E)

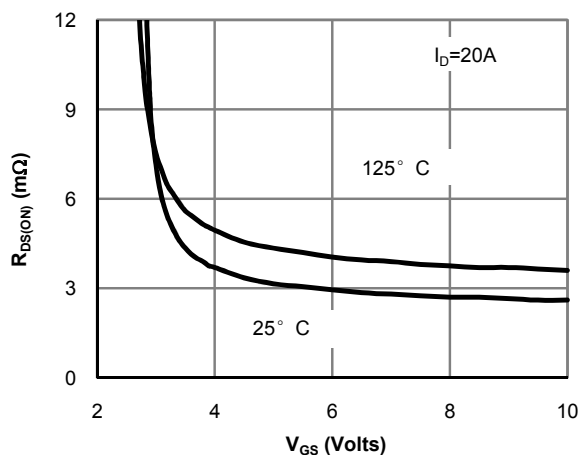


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

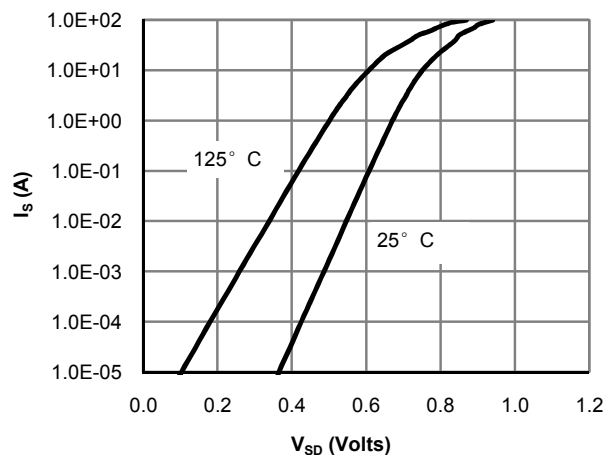


Figure 6: Body-Diode Characteristics (Note E)

N-Channel MOSFET

AO4310 (KO4310)

■ Typical Characteristics

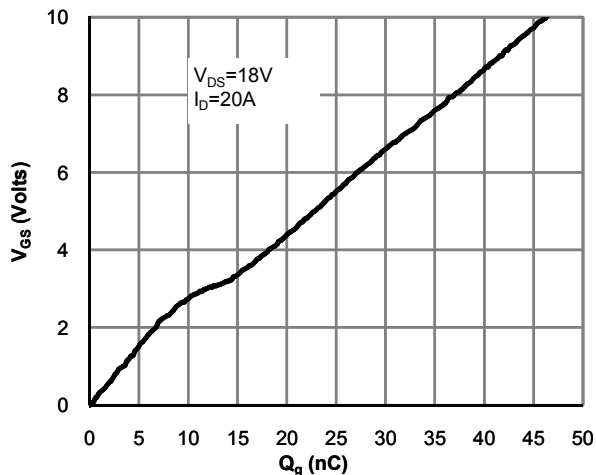


Figure 7: Gate-Charge Characteristics

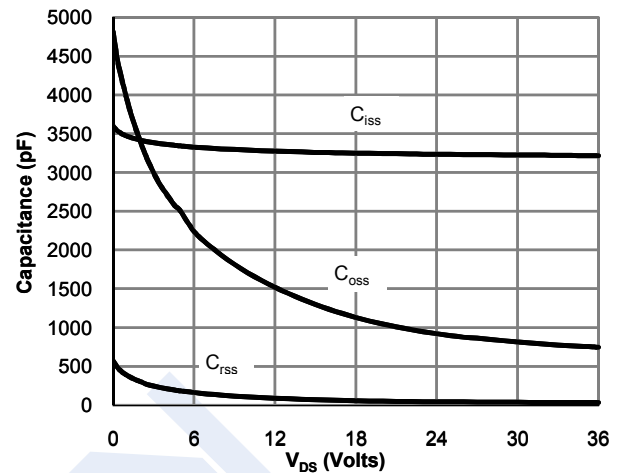


Figure 8: Capacitance Characteristics

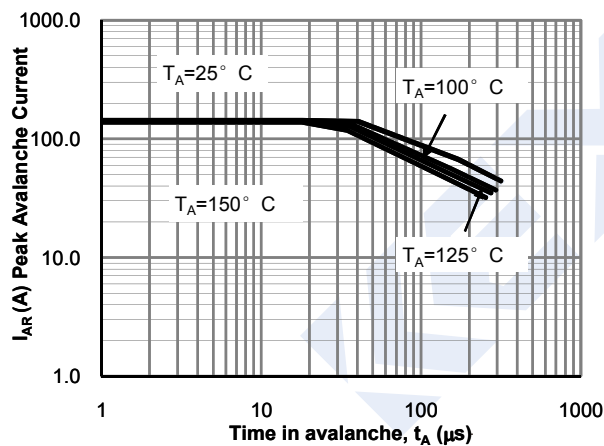


Figure 12: Single Pulse Avalanche capability (Note C)

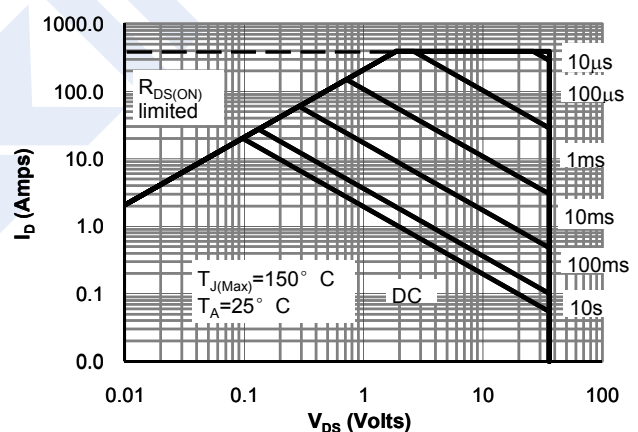


Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

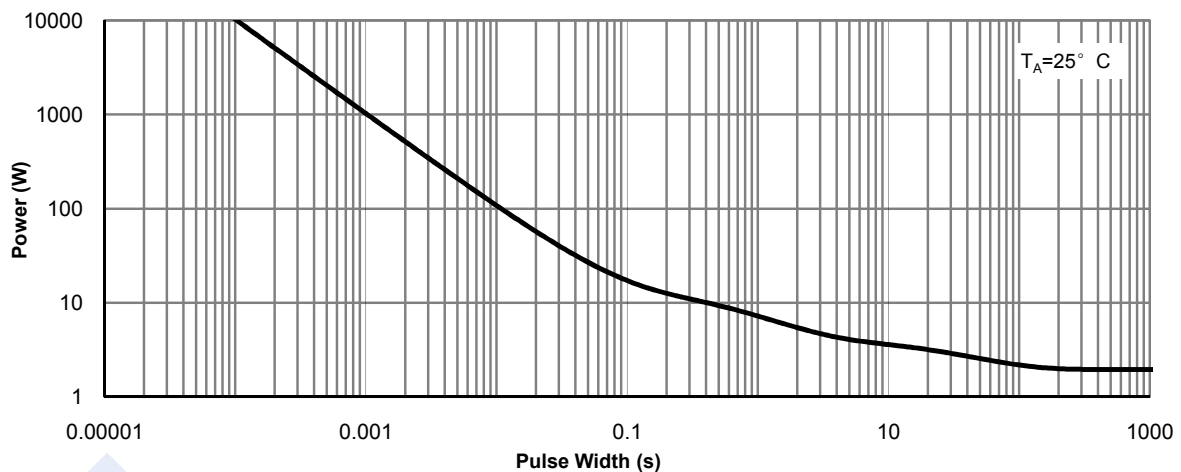


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

N-Channel MOSFET

AO4310 (KO4310)

■ Typical Characteristics

